



KS Conf



AXS2890	MSOP8	AXS2890S XXXXXX XXXX	
	DFN2x2_8L	AXS2890 XXXXXX XXXX	

VIN		6.5	V
VI		-0.3 to VIN+0.3	V
TA		-40°C to 85°C	C
T _J		-40°C to 150°C	C
T _{STG}		-65°C to 150°C	C
T _{SLD}		300°C, 10sec	C

Symbol	Parameter	Test Conditions	MIN	MAX	UNIT
V _{DD}		VDD	2.5	5.5	V
V _{IH}		V _{DD} =2.5V to 5.0V	1.3		V
V _{IL}		V _{DD} =2.5V to 5.0V		0.35	V

ESD

Parameter		Symbol
HBM	Human body model	±1000V
CDM	Charged device model	±250V



(VDD =5V, Gain=20dB, RL =4 , T =25°C, unless otherwise noted.)

Symbol	Parameter	Test Conditions	MIN	TYP	MAX	UNIT
Po		THD+N=10%,f=1KHZ,RL	VDD=5.0V	2.4		W
			VDD=3.6V	1.4		
		THD+N=10%,f=1KHZ,RL	VDD=5.0V	1.7		W
			VDD=3.6V	0.76		
		THD+N=1%,f=1KHZ,RL	VDD=5.0V	1.75		W
			VDD=3.6V	1.05		
		THD+N=1%,f=1KHZ,RL=	VDD=5.0V	1.4		W
			VDD=3.6V	0.6		
THD+N		VDD=5.0V, PO=1W, RL	f=1KHz	0.1		%
		VDD=3.6V, PO=0.5W, RL		0.12		
		VDD=5.0V, PO=1W, RL	f=1KHz	0.14		%
		VDD=3.6V, PO=0.5W, RL		0.15		
PSRR		VDD=4.2V ±200mVp-p	f=1KHz	60		dB
SNR		VDD=5.0V,Vorms=1V, Gv=20dB	f=1KHz	-86		dB
Vn		VDD=5.0V, RL Input floating with Cin	A-weighting	39		
			No A-weighting	53		
		VDD=5.0V, RL Input floating with Cin	A-weighting	22		
			No A-weighting	47		
Dyn		VDD=5.0V, THD=1%	f=1KHz	-95		dB
IQ		VDD=5.0V	No Load	3.5		mA
		VDD=3.0V		2.5		
ISD		VDD=2.5V to 4.2V	VSD=3.3V	1		
Vos		Vin=0V, VDD=5V		20		mV
Tst		Bypass capacitor =1uF		95		mS
OTP		No Load, Junction Temperature	VDD=5.0V	165		°C
OTH				20		

AXS2890

2.4W

AB92 reWnBT/F1.04 T10 0 B34 8 Tm/GS600 G()T10.508 Tm0 G.9.508 T T10

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